WR 8 Bias Tuned Gunn oscillator

Model G 8

The unit utilises a GaAs Gunn device in a waveguide cavity.
The frequency can be adjusted using the applied bias voltage.

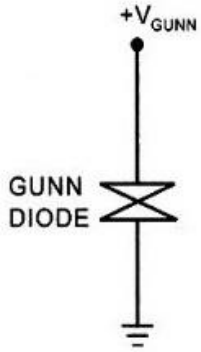
The module provides a convenient way of generating an RF signal using a solid state device.
A clean and stable DC power supply will enhance performance and spectral purity

Applications:-

Educational
Communications
Research
Imaging/ Sensors

Frequency (GHz)	Power		Voltage	Min Bandwidth
number	mW	dBm	volts	(MHz)
140	1	0	~ + 4.0	100
140	2	3.0	~ + 4.0	100
140	3	4.7	~ + 4.0	100

Alternative centre frequency available.
Specifications at + 32ºC case temperature



DC input : SMA female
RF output : UG-387/UM flange compatible

Note: Customised performance and outline envelope available e.g. greater bandwidth, smaller outline/ mass

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135	2	3.0	~ + 4.0	100
135	4	6.0	~ + 4.0	100

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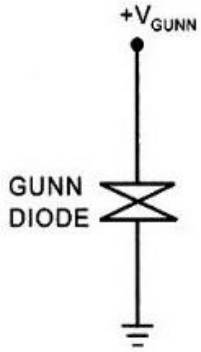

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number	mW	dBm	volts	(MHz)
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130	2	3.0	~ + 4.0	100
130	4	6.0	~ + 4.0	100
130	5	7.0	~ + 4.0	100

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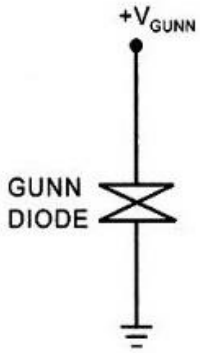

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number	mW	dBm	volts	(MHz)
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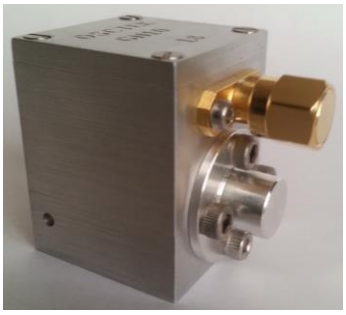
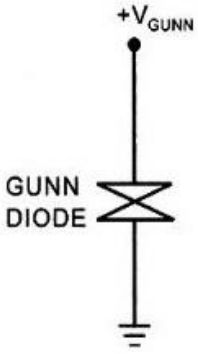
125	5	7.0	~ + 4.0	100
125	10	10.0	~ + 4.0	100

Alternative centre frequency available.
Specifications at + 32ºC case temperature





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number	mW	dBm	volts	(MHz)
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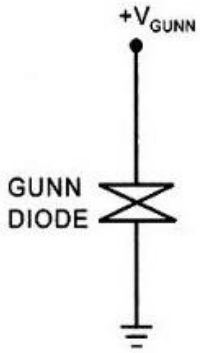
120	5	7.0	~ + 4.0	100
120	10	10.0	~ + 4.0	100
120	15	11.8	~ + 4.0	100

Alternative centre frequency available.
Specifications at + 32ºC case temperature

DC input : SMA female
RF output : UG-387/UM flange compatible



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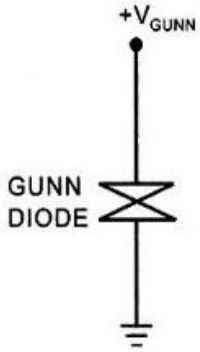
Frequency (GHz)	Power		Voltage	Min Bandwidth
number	mW	dBm	volts	(MHz)
115	1	0	~ + 4.0	100
115	5	7.0	~ + 4.0	100
115	10	10.0	~ + 4.0	100
115	15	11.8	~ + 4.0	100
115	20	13.0	~ + 4.0	100

Alternative centre frequency available.

Specifications at + 32ºC case temperature

DC input : SMA female
RF output : UG-387/UM flange compatible



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